

LOW $V_{CE(SAT)}$ NPN SURFACE MOUNT TRANSISTOR
Features

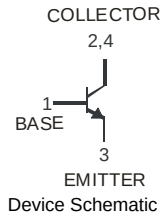
- Complementary PNP Type Available (DSS5540X)
- Ultra Low Collector-Emitter Saturation Voltage
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)**
- "Green" Device (Note 2)**

Mechanical Data

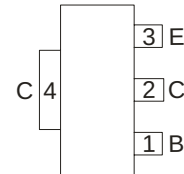
- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072 grams (approximate)



Top View



Device Schematic



Pin Out Configuration

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Continuous Collector Current	I_C	4	A
Repetitive Collector Current (Note 3)	I_{CRM}	5	A
Peak Pulse Collector Current	I_{CM}	10	A
Continuous Base Current	I_B	1	A
Peak Pulse Base Current	I_{BM}	2	A

Thermal Characteristics

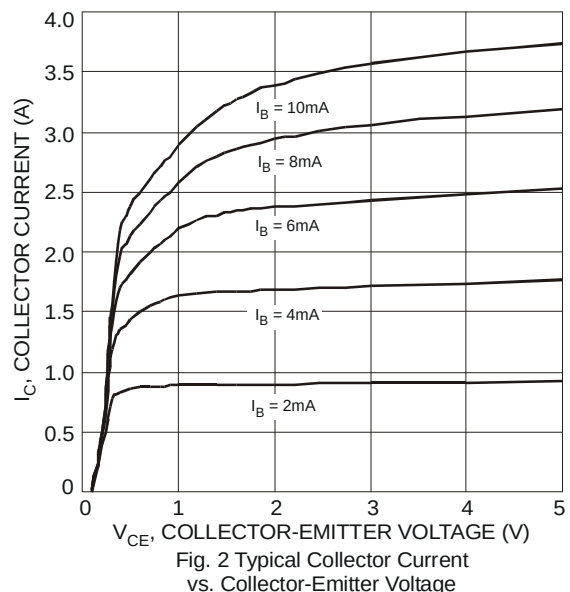
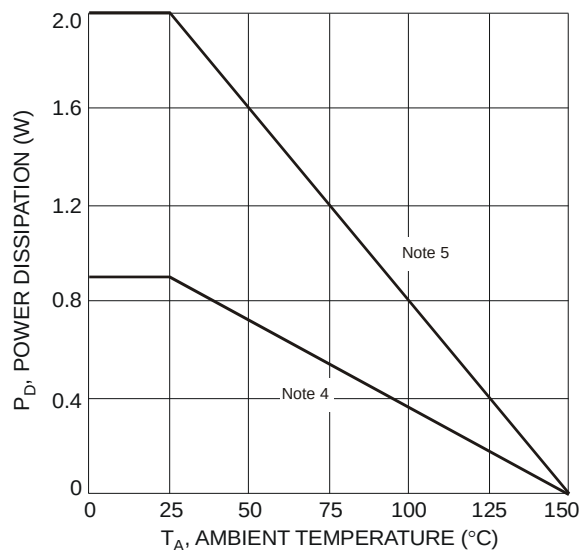
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ $T_A = 25^\circ\text{C}$	P_D	0.9	W
Thermal Resistance, Junction to Ambient Air (Note 4) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	139	$^\circ\text{C/W}$
Power Dissipation (Note 5) @ $T_A = 25^\circ\text{C}$	P_D	2	W
Thermal Resistance, Junction to Ambient Air (Note 5) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
- No purposefully added lead.
 - Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 - Operated under pulsed conditions: pulse width $\leq 10\text{ms}$; duty cycle ≤ 0.2 .
 - Device mounted on FR-4 PCB with minimum recommended pad layout.
 - Device mounted on FR-4 PCB with 1 inch² copper pad layout.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	40	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 6)	V _{(BR)CEO}	40	—	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6	—	—	V	I _E = 100μA
Collector-Base Cutoff Current	I _{CBO}	—	—	100	nA	V _{CB} = 30V, I _E = 0
		—	—	50	μA	V _{CB} = 30V, I _E = 0, T _A = 150°C
Collector-Emitter Cut-Off Current	I _{CES}	—	—	100	nA	V _{CE} = 30V, V _{BE} = 0V
Emitter-Base Cutoff Current	I _{EBO}	—	—	100	nA	V _{EB} = 5V, I _C = 0
ON CHARACTERISTICS (Note 6)						
DC Current Gain	h _{FE}	300	—	—	—	V _{CE} = 2V, I _C = 0.5A
		300	—	—	—	V _{CE} = 2V, I _C = 1A
		250	—	—	—	V _{CE} = 2V, I _C = 2A
		100	—	—	—	V _{CE} = 2V, I _C = 5A
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	—	90	mV	I _C = 0.5A, I _B = 5mA
		—	—	120	mV	I _C = 1A, I _B = 10mA
		—	80	150	mV	I _C = 2A, I _B = 200mA
		—	160	290	mV	I _C = 4A, I _B = 200mA
		—	185	355	mV	I _C = 5A, I _B = 500mA
Equivalent On-Resistance	R _{CE(SAT)}	—	37	71	mΩ	I _C = 5A, I _B = 500mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	—	1.1	V	I _C = 4A, I _B = 200mA
		—	—	1.2	V	I _C = 5A, I _B = 500mA
Base-Emitter Turn-on Voltage	V _{BE(ON)}	—	—	1.1	V	V _{CE} = 2V, I _C = 2A
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	70	—	—	MHz	V _{CE} = 10V, I _C = 0.1A, f = 100MHz
Collector Capacitance	C _C	—	—	75	pF	V _{CB} = 10V, I _E = 0A, f = 1MHz
SWITCHING CHARACTERISTICS						
Turn-On Time	t _{on}	—	135	—	ns	V _{CC} = 10V, I _C = 2A, I _{B1} = 40mA
Delay Time	t _d	—	60	—	ns	
Rise Time	t _r	—	75	—	ns	
Turn-Off Time	t _{off}	—	670	—	ns	V _{CC} = 10V, I _C = 2A, I _{B1} = I _{B2} = 40mA
Storage Time	t _s	—	570	—	ns	
Fall Time	t _f	—	100	—	ns	

Notes: 6. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.



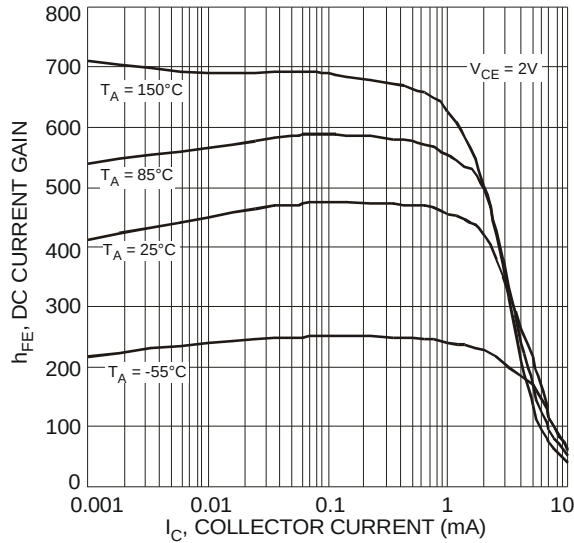


Fig. 3 Typical DC Current Gain vs. Collector Current

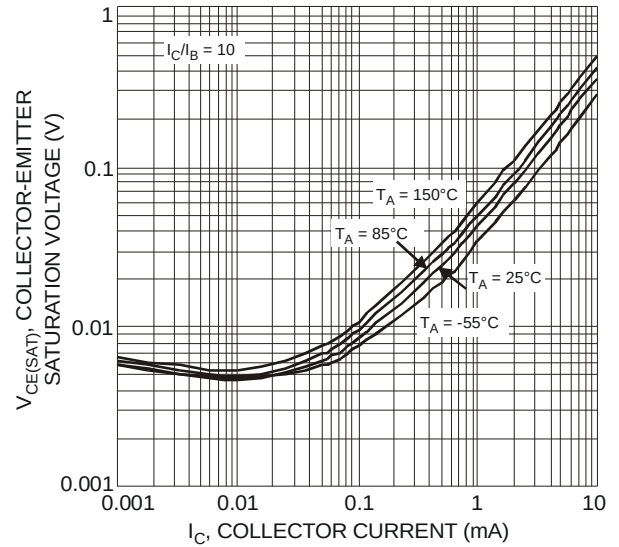


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

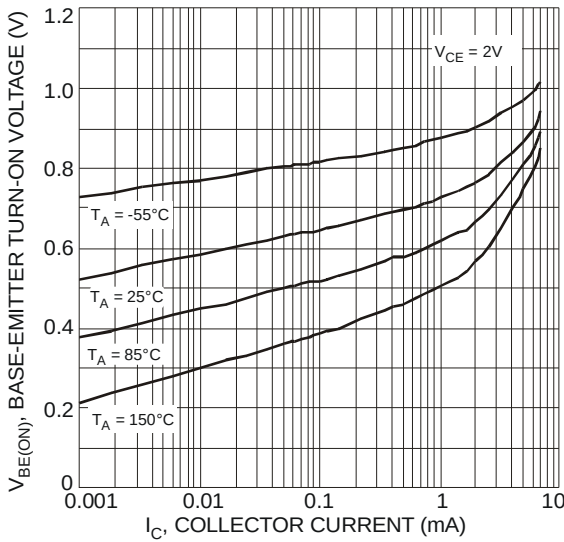


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

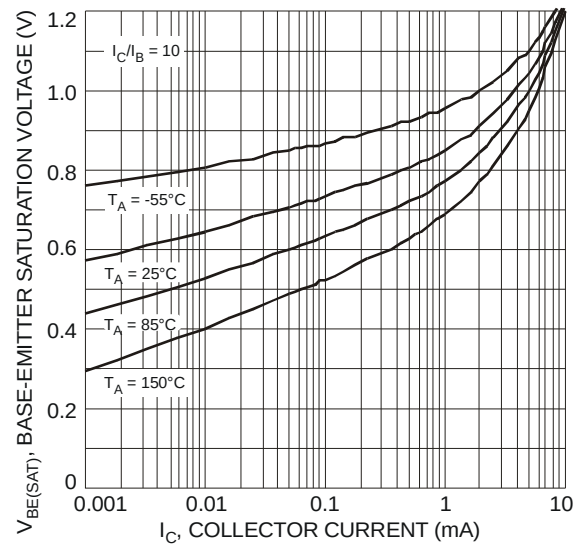


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

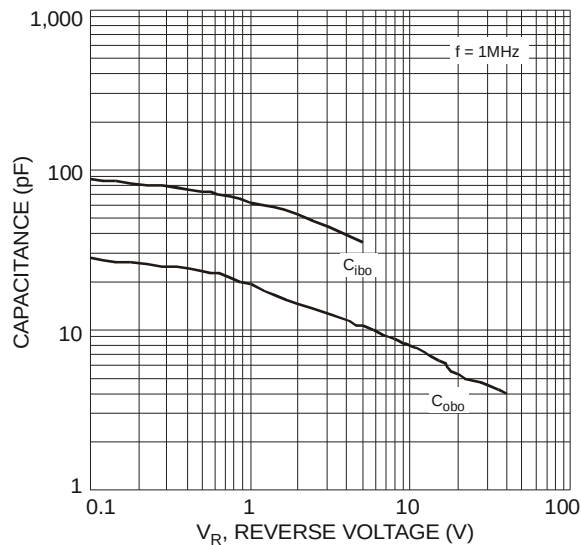


Fig. 7 Typical Capacitance Characteristics

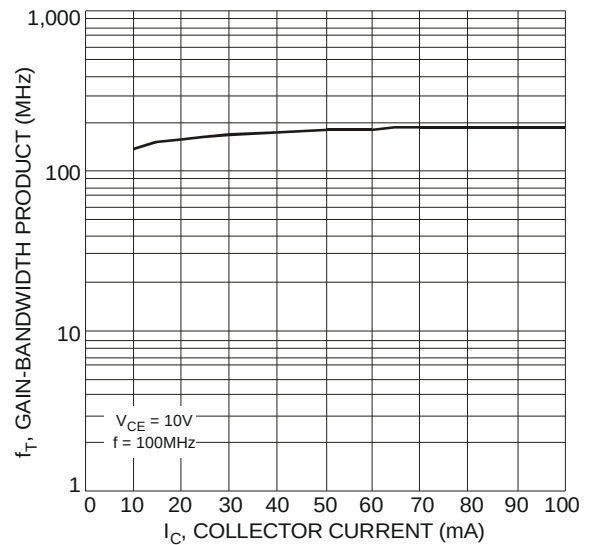


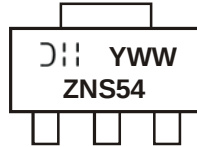
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Ordering Information (Note 7)

Part Number	Case	Packaging
DSS4540X-13	SOT89-3L	2500/Tape & Reel

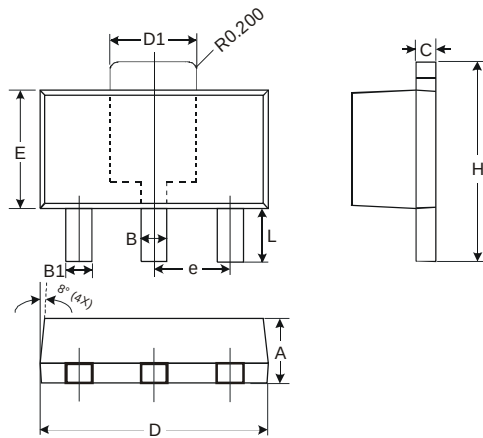
Notes: 7. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



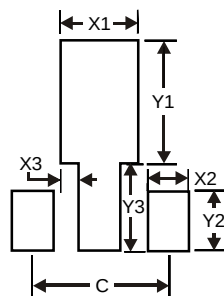
ZNS54 = Product Type Marking Code
 ⌐ = Manufacturer's Code Marking
 YWW = Date Code Marking
 Y = Last digit of year (ex: 8 = 2008)
 WW = Week code 01 - 52

Package Outline Dimensions



SOT89-3L			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.45	0.55	0.50
B1	0.37	0.47	0.42
C	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.50	1.70	1.60
E	2.40	2.60	2.50
e	—	—	1.50
H	3.95	4.25	4.10
L	0.90	1.20	1.05
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
X1	1.7
X2	0.9
X3	0.4
Y1	2.7
Y2	1.3
Y3	1.9
C	3.0

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